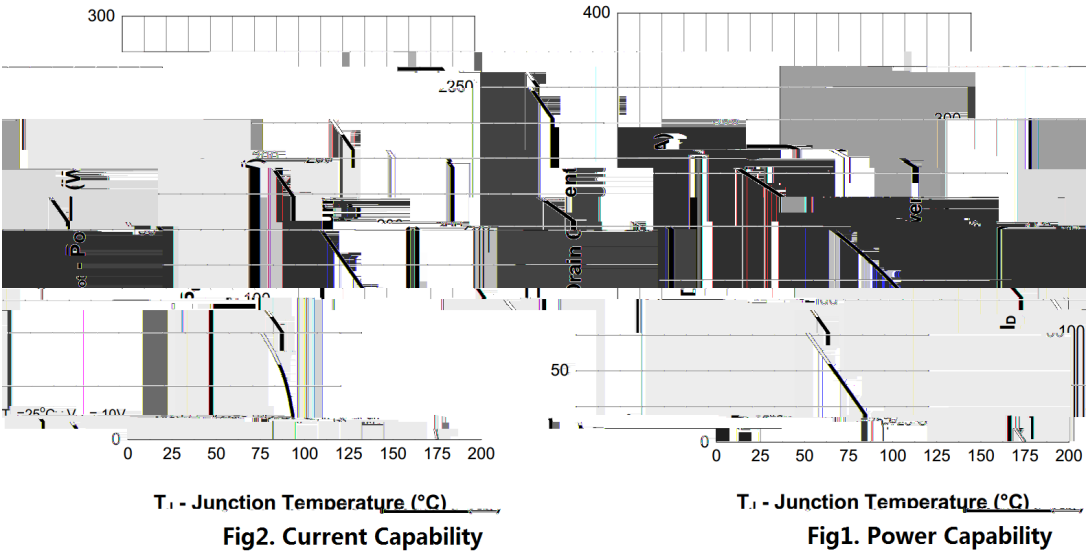
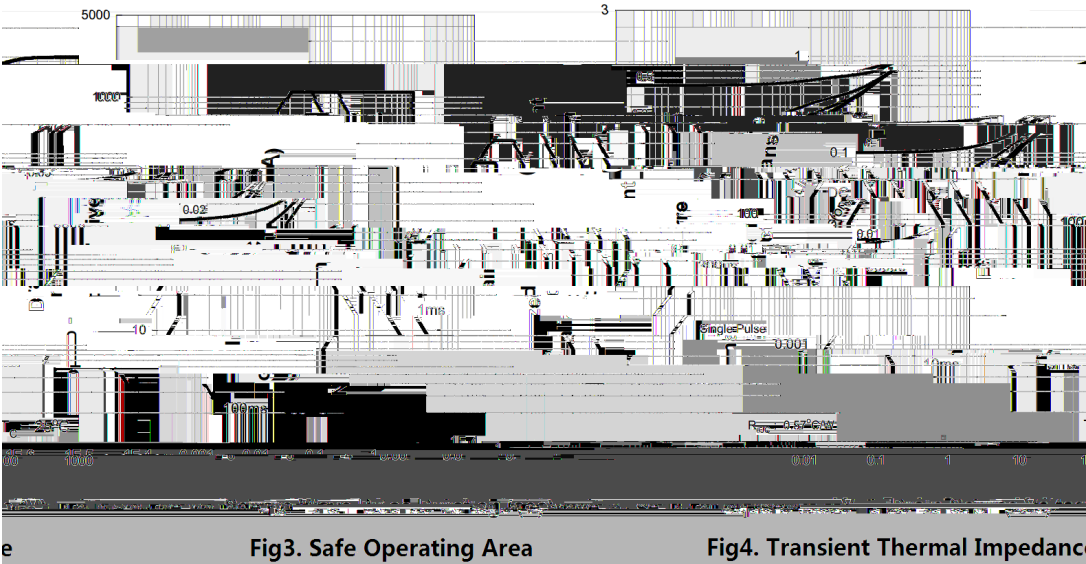
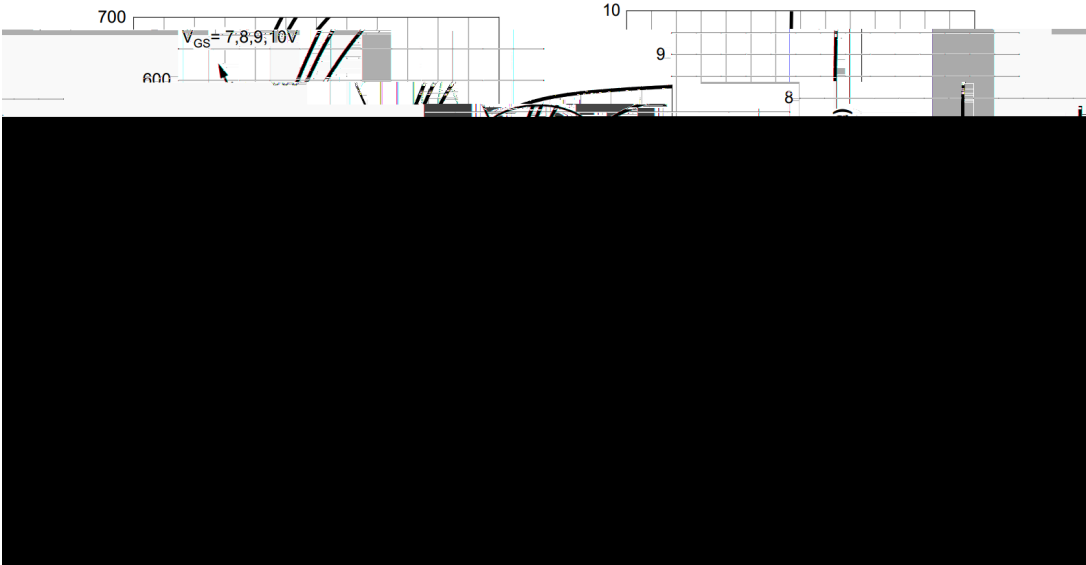




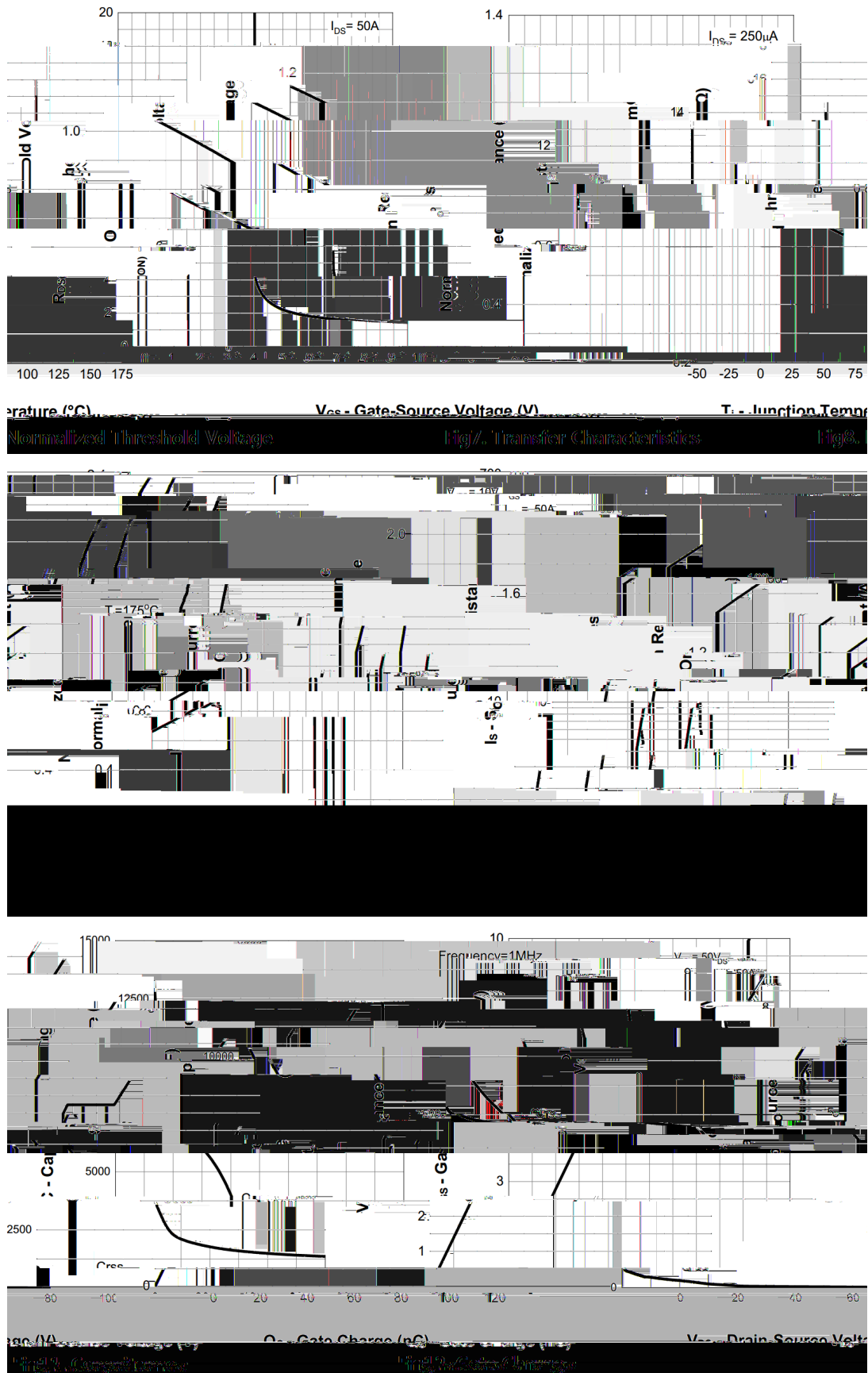
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current(DC)	$I_D(T_C=25^\circ\text{C})$	275	A
	$I_D(T_C=100^\circ\text{C})$	194	A
Drain Current – Pulsed	I_{DM}	1100	A
Power Dissipation	P_{tot}	263	W
Junction and Storage Temperature Range	T_j, T_{stg}	-55 to 175	$^\circ\text{C}$
Continuous-Source Current	I_S	275	A
Single Pulse Avalanche Energy ($V_{DD}=50\text{V}, L=1.0\text{mH}$)	E_{AS}	2450	mJ
Thermal resistance, junction - Ambient	R_{JA}	45	$^\circ\text{C/W}$
Thermal resistance, junction - case	R_{JC}	0.57	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D=250\mu\text{A}, V_{GS}=0\text{V}$	100			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	2		4	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=80\text{V}, V_{GS}=0\text{V}$			1	μA
Gate-Body leakage current	I_{GSS}	$V_{DS}=0\text{V}, V_{GS}=\pm 20\text{V}$			± 100	nA

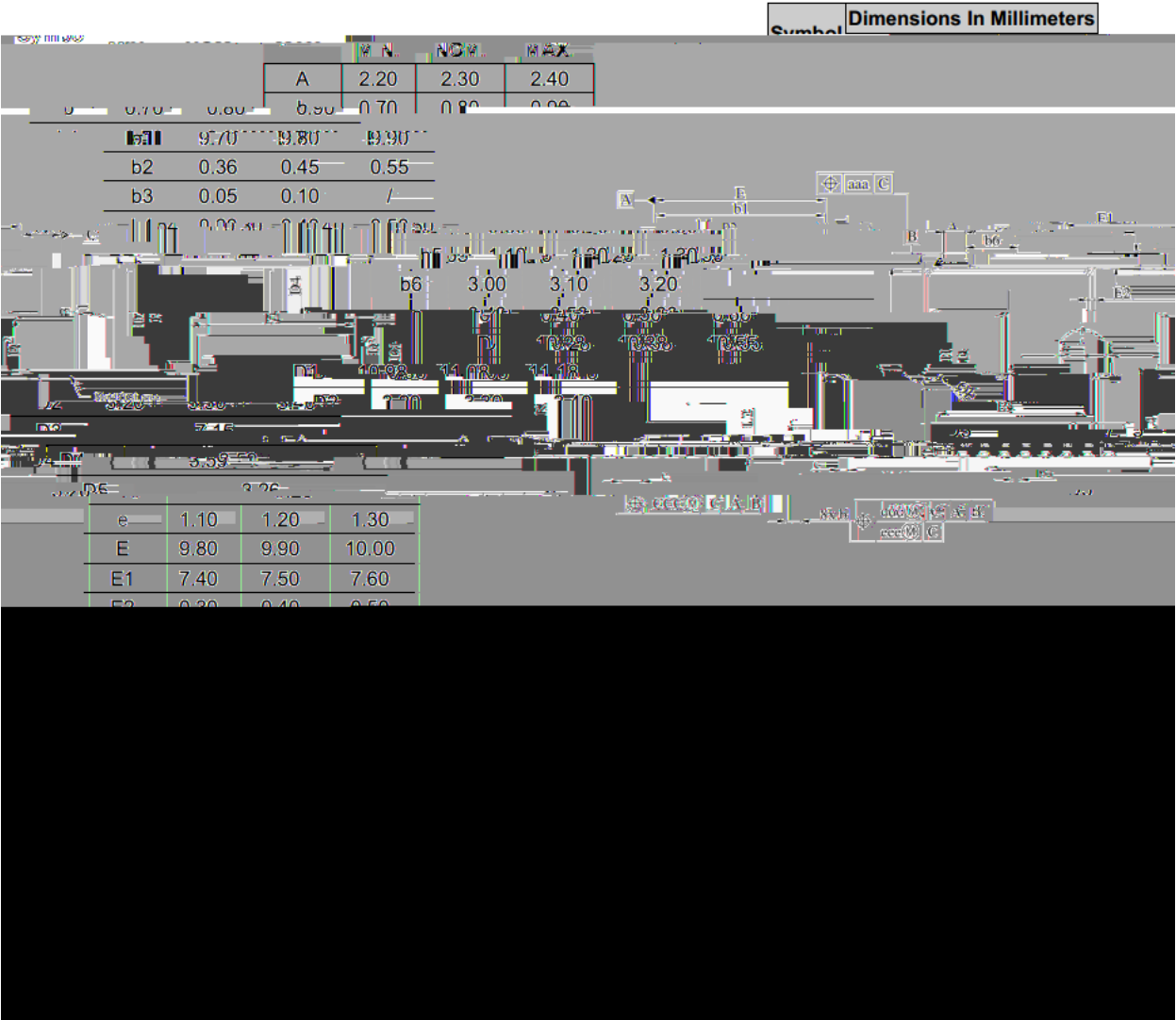
/ Electrical Characteristic Curve



/ Electrical Characteristic Curve



/ Package Dimensions



BRCS017N10SHTL
Rev.A Aug-2026